



PATENT  
Customer No. 22,852  
Attorney Docket No. 07553.0029-00000

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Masaaki HAGIHARA et al. ) Group Art Unit: 1763  
)  
Application No.: 10/030,656 ) Examiner: A. Olsen  
)  
Filed: January 11, 2002 )  
)  
For: ETCHING METHOD AND )  
PLASMA PROCESSING )  
METHOD )

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6/19/03  
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JUN 16 2003  
TC 1700

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

AMENDMENT

In reply to the Office Action dated March 20, 2003, please amend the application as follows:

IN THE CLAIMS:

Please cancel claims 1-3 and 5 without prejudice or disclaimer, amend claims 4 and 6, and add new claim 12, as follows:

4. (Amended) An etching method for exposing a layer of Cu by etching a layer of  $\text{SiN}_x$  on the layer of Cu with an etching gas constituted of C, H, and F, wherein; said gas constituted of C, H, and F is  $\text{CHF}_3$ .